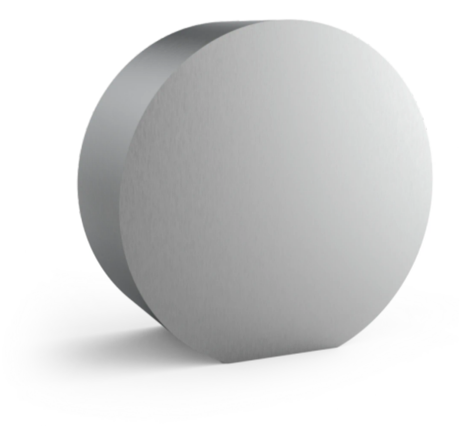
Single crystal gallium arsenide



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Growing method	VGF
ominal diameter, mm	100
Deviation from nominal value, μm	+1/-0
ystallographic orientation, °	(100)
nductivity type	N
pant	Si
harge carrier mobility, $cm^2/V\cdot sec$	> 1200
harge carrier concentration, cm-3	From $1\cdot10^{17}$ to $3\cdot10^{18}$
Dislocation density, cm-2	< 500